

# 11E1 - 11E6

# SILICON RECTIFIER DIODES

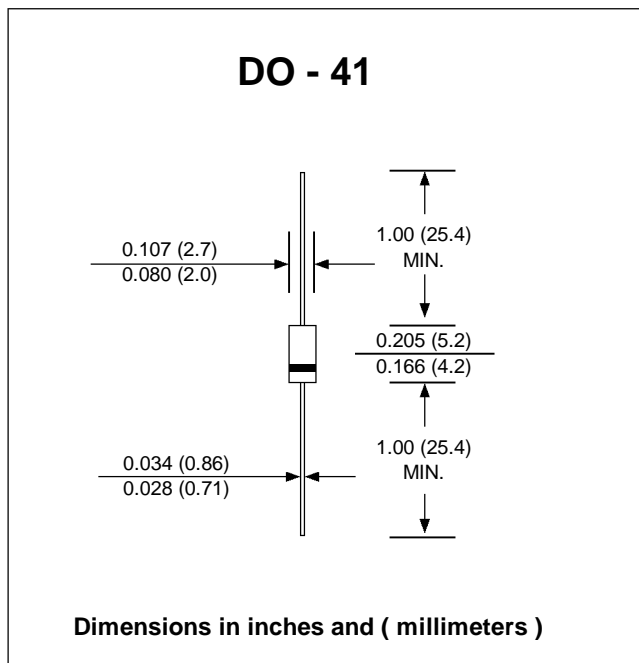
**PRV : 100 - 600 Volts**  
**Io : 1.0 Ampere**

**FEATURES :**

- \* High current capability
- \* High surge current capability
- \* High reliability
- \* Low reverse current
- \* Low forward voltage drop
- \* **Pb / RoHS Free**

**MECHANICAL DATA :**

- \* Case : DO-41 Molded plastic
- \* Epoxy : UL94V-O rate flame retardant
- \* Lead : Axial lead solderable per MIL-STD-202, Method 208 guaranteed
- \* Polarity : Color band denotes cathode end
- \* Mounting position : Any
- \* Weight : 0.339 gram



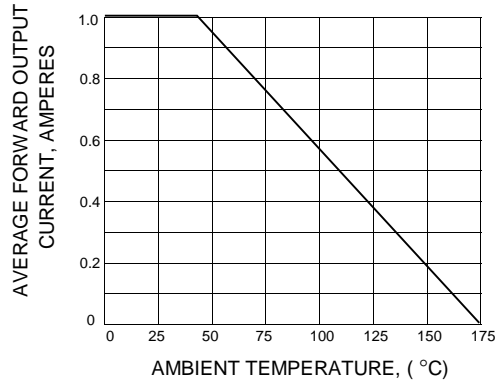
**MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS**

Rating at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%.

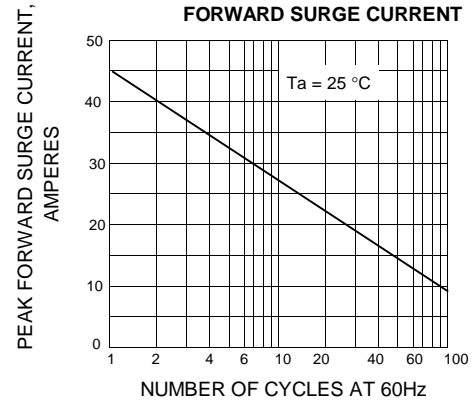
RATING	SYMBOL	11E1	11E2	11E4	11E6	UNIT
Maximum Repetitive Peak Reverse Voltage	V <sub>RRM</sub>	100	200	400	600	V
Maximum RMS Voltage	V <sub>RMS</sub>	70	140	280	420	V
Maximum DC Blocking Voltage	V <sub>DC</sub>	100	200	400	600	V
Maximum Average Forward Current Ta = 40°C	I <sub>F</sub>	1.0				A
Maximum Peak Forward Surge Current	I <sub>FSM</sub>	45				A
Maximum Forward Voltage at I <sub>F</sub> = 1.0 A	V <sub>F</sub>	1.0				V
Maximum Reverse Current at V <sub>R</sub> = V <sub>RRM</sub>	I <sub>RM</sub>	50	10			μA
Junction Temperature Range	T <sub>J</sub>	- 65 to + 175				°C
Storage Temperature Range	T <sub>STG</sub>	- 65 to + 175				°C

### RATING AND CHARACTERISTIC CURVES ( 11E1 - 11E6 )

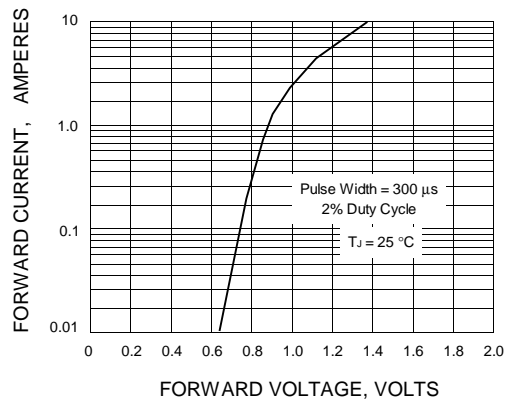
**FIG.1 - DERATING CURVE FOR OUTPUT RECTIFIED CURRENT**



**FIG.2 - MAXIMUM NON-REPETITIVE PEAK FORWARD SURGE CURRENT**



**FIG.3 - TYPICAL FORWARD CHARACTERISTICS**



**FIG.4 - TYPICAL REVERSE CHARACTERISTICS**

